

Smart High-Side Power Switch for Industrial Applications

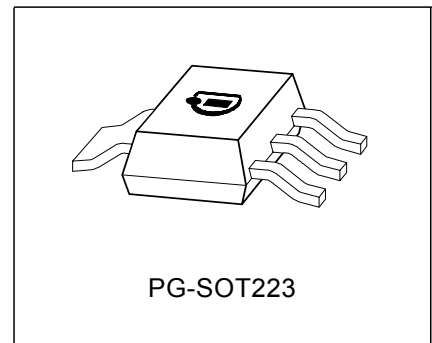
1 Channel: 1 x 200mΩ

Features

- Short circuit protection
- Current limitation
- Overload protection
- Overvoltage protection (including load dump)
- Undervoltage shutdown with auto-restart and hysteresis
- Switching inductive loads
- Clamp of negative voltage at output with inductive loads
- CMOS compatible input
- Thermal shutdown with restart
- ESD - Protection
- Loss of GND and loss of V_{bb} protection
- Very low standby current
- Reverse battery protection with external resistor
- Improved electromagnetic compatibility (EMC)

Product Summary

| | | | |
|------------------------|--------------|-----------|----|
| Overvoltage protection | $V_{bb(AZ)}$ | 47 | V |
| Operating voltage | $V_{bb(on)}$ | 12...45 | V |
| On-state resistance | R_{ON} | 200 | mΩ |
| Operating temperature | T_a | -30...+85 | °C |



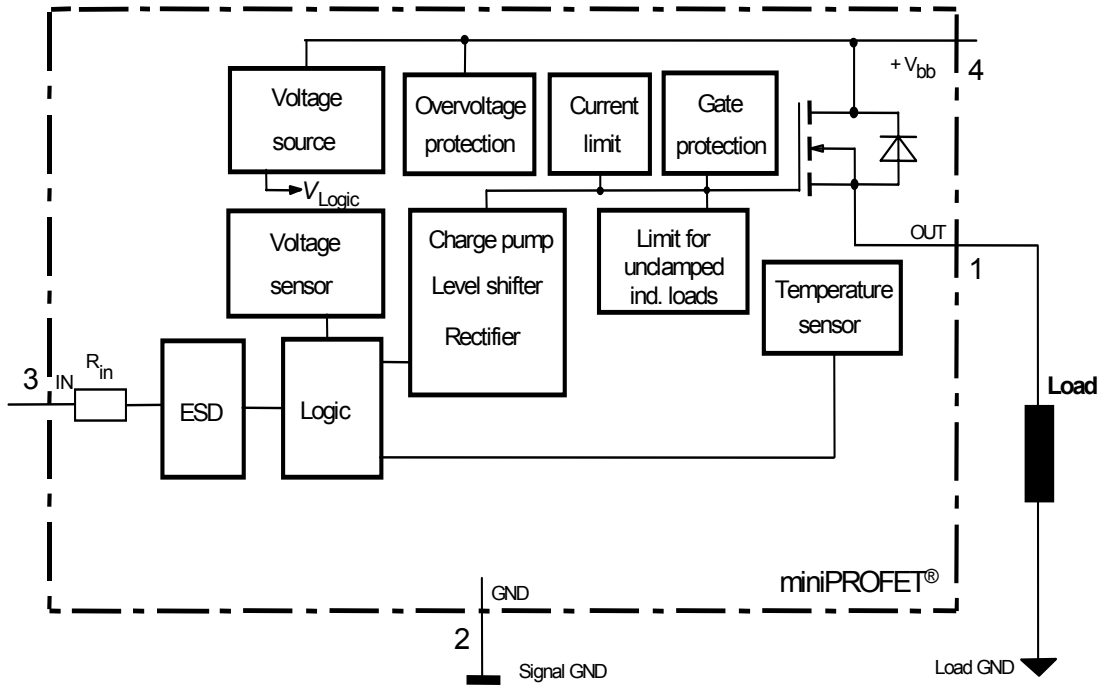
Application

- All types of resistive, inductive and capacitive loads
- μ C compatible power switch for 12 V and 24 V DC industrial applications
- Replaces electromechanical relays and discrete circuits

General Description

N channel vertical power FET with charge pump, ground referenced CMOS compatible input, monolithically integrated in Smart SIPMOS® technology. Providing embedded protective functions.

Block Diagram



| Pin | Symbol | Function |
|-----|--------|--|
| 1 | OUT | Output to the load |
| 2 | GND | Logic ground |
| 3 | IN | Input, activates the power switch in case of logic high signal |
| 4 | Vbb | Positive power supply voltage |

Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|----------------|--------------------------|------------------|
| at $T_j = 25^\circ\text{C}$, unless otherwise specified | | | |
| Supply voltage | V_{bb} | -0,3 ¹⁾ ...48 | V |
| Continuous input voltage ²⁾ | V_{IN} | -10... V_{bb} | |
| Load current (Short - circuit current, see page 5) | I_L | self limited | A |
| Current through input pin (DC) | I_{IN} | ± 5 | mA |
| Reverse current through GND-pin ³⁾ | $-I_{GND}$ | -0.5 | A |
| Junction temperature | T_j | internal limited | $^\circ\text{C}$ |
| Operating temperature | T_a | -30...+85 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -40 ... +105 | $^\circ\text{C}$ |
| Power dissipation ⁴⁾ | P_{tot} | 1.4 | W |
| Inductive load switch-off energy dissipation ⁴⁾⁵⁾ single pulse $T_j = 125^\circ\text{C}$, $I_L = 1\text{ A}$ | E_{AS} | 0.16 | J |
| Load dump protection ⁵⁾ $V_{LoadDump}^{6)} = V_A + V_S$ $R_I = 2\Omega$, $t_d = 400\text{ms}$, $V_{IN} = \text{low or high}$, $V_A = 13,5\text{V}$ $R_L = 47\ \Omega$ | $V_{Loaddump}$ | 83 | V |
| Electrostatic discharge voltage (Human Body Model) according to ANSI EOS/ESD - S5.1 - 1993 ESD STM5.1 - 1998 | V_{ESD} | | kV |
| Input pin | | ± 1 | |
| All other pins | | ± 5 | |

¹defined by P_{tot}

²At $V_{IN} > V_{bb}$, the input current is not allowed to exceed $\pm 5\text{ mA}$.

³defined by P_{tot}

⁴Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for V_{bb} connection. PCB is vertical without blown air.

⁵not subject to production test, specified by design

⁶ $V_{Loaddump}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839 .

Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND pin, e.g. with a 150 Ω resistor in GND connection. A resistor for the protection of the input is integrated.

Electrical Characteristics

| Parameter at $T_j = -40 \dots 125 \text{ }^\circ\text{C}$, $V_{bb} = 15 \dots 30 \text{ V}$ unless otherwise specified | Symbol | Values | | | Unit |
|--|--------|--------|------|------|------|
| | | min. | typ. | max. | |

Thermal Characteristics

| | | | | | |
|---|--------------|---|---|-----|-----|
| Thermal resistance @ min. footprint | $R_{th(JA)}$ | - | - | 125 | K/W |
| Thermal resistance @ 6 cm ² cooling area ¹⁾ | $R_{th(JA)}$ | - | - | 70 | |
| Thermal resistance, junction - soldering point | $R_{th(JS)}$ | - | - | 7 | K/W |

Load Switching Capabilities and Characteristics

| | | | | | |
|--|----------------|-----|-----|-----|------|
| On-state resistance $T_j = 25 \text{ }^\circ\text{C}$, $I_L = 0.5 \text{ A}$ $T_j = 125 \text{ }^\circ\text{C}$ | R_{ON} | - | 150 | 200 | mΩ |
| | | - | 270 | 320 | |
| Nominal load current ²⁾ Device on PCB ¹⁾ | $I_{L(nom)}$ | 1.4 | - | - | A |
| Turn-on time to 90% V_{OUT} $R_L = 47 \text{ } \Omega$, $V_{IN} = 0 \text{ to } 10 \text{ V}$ | t_{on} | - | 50 | 100 | μs |
| Turn-off time to 10% V_{OUT} $R_L = 47 \text{ } \Omega$, $V_{IN} = 10 \text{ to } 0 \text{ V}$ | t_{off} | - | 75 | 150 | |
| Slew rate on 10 to 30% V_{OUT} , $R_L = 47 \text{ } \Omega$, $V_{bb} = 15 \text{ V}$ | dV/dt_{on} | - | 1 | 2 | V/μs |
| Slew rate off 70 to 40% V_{OUT} , $R_L = 47 \text{ } \Omega$, $V_{bb} = 15 \text{ V}$ | $-dV/dt_{off}$ | - | 1 | 2 | |

¹Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air.

²Nominal load current is limited by the current limitation (see page 5)

Electrical Characteristics

| Parameter | Symbol | Values | | | Unit |
|---|-------------------------------|--------|------|------|---------------|
| | | min. | typ. | max. | |
| at $T_j = -40 \dots 125 \text{ }^\circ\text{C}$, $V_{bb} = 15 \dots 30 \text{ V}$ unless otherwise specified | | | | | |
| Operating Parameters | | | | | |
| Operating voltage | $V_{bb(\text{on})}$ | 12 | - | 45 | V |
| Undervoltage shutdown | $V_{bb(\text{under})}$ | 7 | - | 10.5 | |
| Undervoltage restart | $V_{bb(\text{u rst})}$ | - | - | 11 | |
| Undervoltage hysteresis $\Delta V_{bb(\text{under})} = V_{bb(\text{u rst})} - V_{bb(\text{under})}$ | $\Delta V_{bb(\text{under})}$ | - | 0.5 | - | |
| Standby current $T_j = -40 \dots 85 \text{ }^\circ\text{C}$, $V_{IN} \leq 1,2 \text{ V}$ $T_j = 125 \text{ }^\circ\text{C}^1)$ | $I_{bb(\text{off})}$ | - | 10 | 25 | μA |
| | | - | - | 50 | |
| Operating current | I_{GND} | - | 1 | 1.6 | mA |
| Leakage output current (included in $I_{bb(\text{off})}$) $V_{IN} \leq 1,2 \text{ V}$ | $I_{\text{L}(\text{off})}$ | - | 3.5 | 10 | μA |

Protection Functions²⁾

| | | | | | |
|--|----------------------------|-----|-----|-----|------------------|
| Initial peak short circuit current limit $T_j = -40 \text{ }^\circ\text{C}$, $V_{bb} = 20 \text{ V}$, $t_m = 150 \text{ } \mu\text{s}$ $T_j = 25 \text{ }^\circ\text{C}$ $T_j = 125 \text{ }^\circ\text{C}$ | $I_{\text{L}(\text{SCp})}$ | - | - | 4.5 | A |
| | | - | 3 | - | |
| | | 1.4 | - | - | |
| Repetitive short circuit current limit $T_j = T_{jt}$ (see timing diagrams) | $I_{\text{L}(\text{SCr})}$ | - | 2.2 | - | |
| Output clamp (inductive load switch off) at $V_{\text{OUT}} = V_{bb} - V_{\text{ON}(\text{CL})}$, $I_{bb} = 4 \text{ mA}$ | $V_{\text{ON}(\text{CL})}$ | 62 | 68 | - | V |
| Overvoltage protection ³⁾ $I_{bb} = 4 \text{ mA}$ | $V_{bb(\text{AZ})}$ | 47 | - | - | |
| Thermal overload trip temperature ⁴⁾ | T_{jt} | 135 | - | - | $^\circ\text{C}$ |
| Thermal hysteresis | ΔT_{jt} | - | 10 | - | K |

¹higher current due temperature sensor

²Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

³see also $V_{\text{ON}(\text{CL})}$ in circuit diagram

⁴ higher operating temperature at normal function available

Electrical Characteristics

| Parameter at $T_j = -40...125\text{ °C}$, $V_{bb} = 15...30\text{ V}$ unless otherwise specified | Symbol | Values | | | Unit |
|--|--------------------|-------------------|------|----------|------------------|
| | | min. | typ. | max. | |
| Input | | | | | |
| Continuous input voltage ¹⁾ | V_{IN} | -10 ²⁾ | - | V_{bb} | V |
| Input turn-on threshold voltage | $V_{IN(T+)}$ | - | - | 3.0 | |
| Input turn-off threshold voltage | $V_{IN(T-)}$ | 1.82 | - | - | |
| Input threshold hysteresis | $\Delta V_{IN(T)}$ | - | 0.2 | - | |
| Off state input current $V_{IN} \leq 1,8\text{ V}$ | $I_{IN(off)}$ | 20 | - | - | μA |
| On state input current | $I_{IN(on)}$ | - | - | 110 | |
| Input delay time at switch on V_{bb} | $t_d(V_{bbon})$ | 150 | 340 | - | μs |
| Input resistance (see page 8) | R_I | 1.5 | 3 | 5 | $\text{k}\Omega$ |

Reverse Battery

| | | | | | |
|---|-----------|---|-----|-----------|---|
| Reverse battery voltage ³⁾²⁾ $R_{GND} = 0\ \Omega$ $R_{GND} = 150\ \Omega$ | $-V_{bb}$ | - | - | 0.3 45 | V |
| Continuous reverse drain current ²⁾ $T_j = 25\text{ °C}$ | I_S | - | - | 1 | A |
| Drain-source diode voltage ($V_{OUT} > V_{bb}$) $I_F = 1\text{ A}$ | $-V_{ON}$ | - | 0.6 | 1.2 | V |

¹At $V_{IN} > V_{bb}$, the input current is not allowed to exceed $\pm 5\text{ mA}$.

²not subject to production test, guaranteed by design

³defined by P_{tot}

EMC-Characteristics

All EMC-Characteristics are based on limited number of samples and no part of production test.

Test Conditions:

If not other specified the test circuitry is the minimal functional configuration without any external components for protection or filtering.

| | | | |
|-----------------|-------------------|--------------|----------------------------|
| Supply voltage: | $V_{bb} = 13.5V$ | Temperature: | $T_a = 23 \pm 5^\circ C$; |
| Load: | $R_L = 220\Omega$ | | |
| Operation mode: | PWM DC On/Off | Frequency: | 100Hz / Duty Cycle: 50% |
| DUT-Specific.: | R_{GND} | | |

Fast electrical transients

Acc. ISO 7637

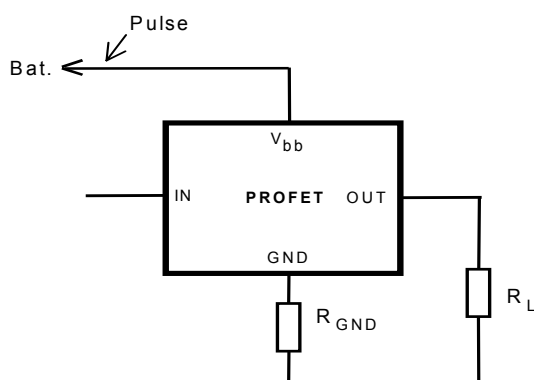
| Test Pulse | Test Level | Test Results | | Pulse Cycle Time and Generator Impedance |
|-----------------|------------|--------------|---------|--|
| | | On | Off | |
| 1 | -200 V | C | C | 500ms ; 10 Ω |
| 2 | +200 V | C | C | 500ms ; 10 Ω |
| 3a | -200 V | C | C | 100ms ; 50 Ω |
| 3b | + 200 V | C | C | 100ms ; 50 Ω |
| 4 ¹⁾ | -7 V | C | C | 0,01 Ω |
| 5 | 175 V | E (70V) | E (70V) | 400ms ; 2 Ω |

The test pulses are applied at V_{bb}

Definition of functional status

| Class | Content |
|-------|--|
| C | All functions of the device are performed as designed after exposure to disturbance. |
| E | One or more function of a device does not perform as designed after exposure and can not be returned to proper operation without repairing or replacing the device. The value after the character shows the limit. |

Test circuit:

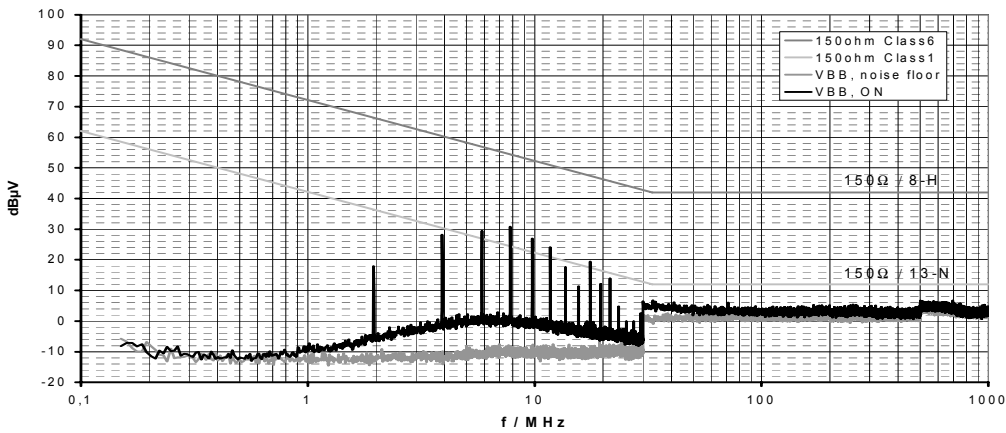


¹Supply voltage $V_{bb} = 12 V$ instead of 13,5 V.

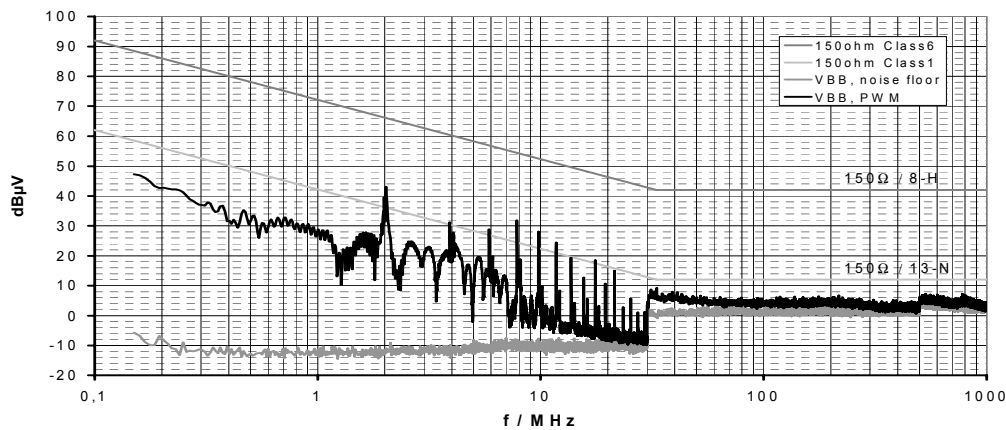
Conducted Emission

Acc. IEC 61967-4 (1Ω / 150Ω method)

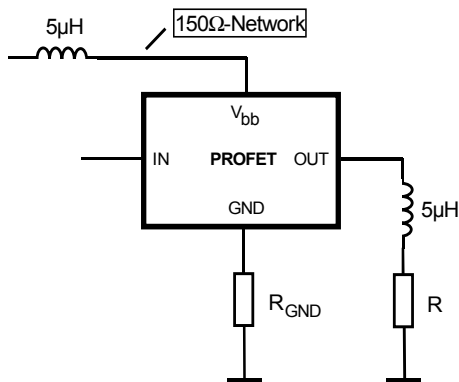
Typ. V_{bb} -Pin Emission at DC-On with 150Ω-matching network



Typ. V_{bb} -Pin Emission at PWM-Mode with 150Ω-matching network



Test circuit:



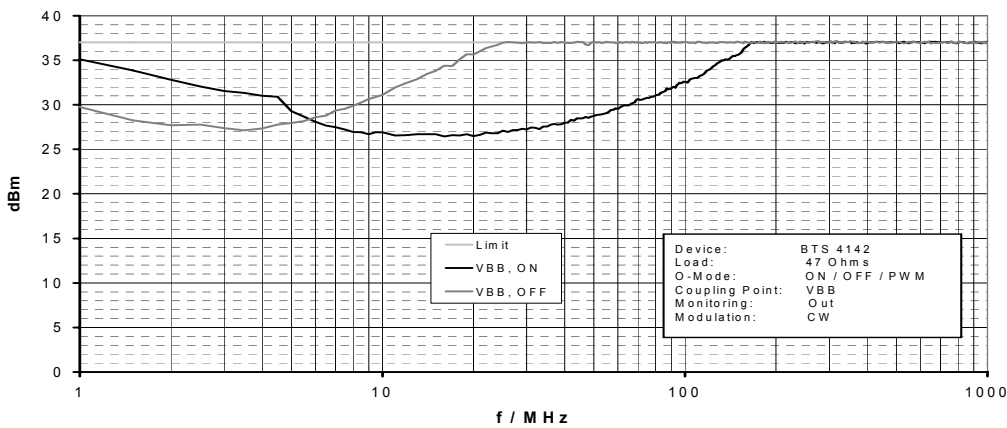
For defined decoupling and high reproducibility a defined choke (5μH at 1 MHz) is inserted between supply and V_{bb} -pin.

Conducted Susceptibility

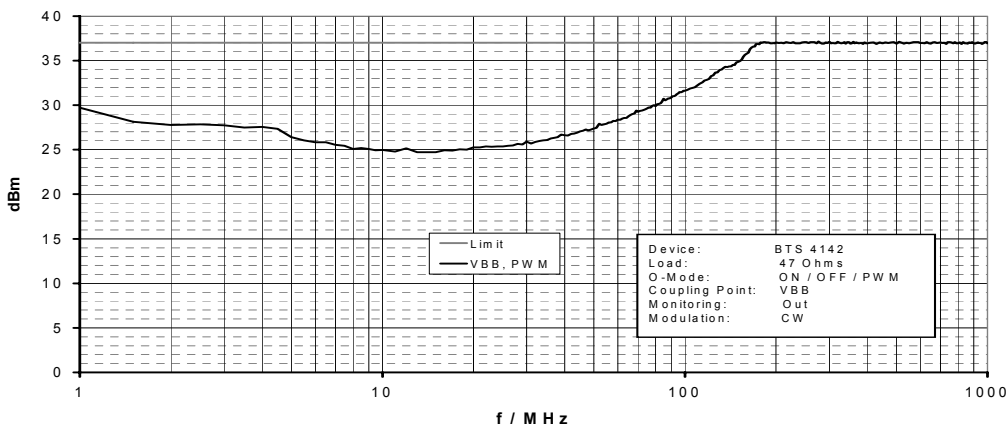
Acc. 47A/658/CD IEC 62132-4 (Direct Power Injection)

Direct Power Injection: Forward Power CW
Failure criteria: Amplitude and frequency deviation max. 10% at Out

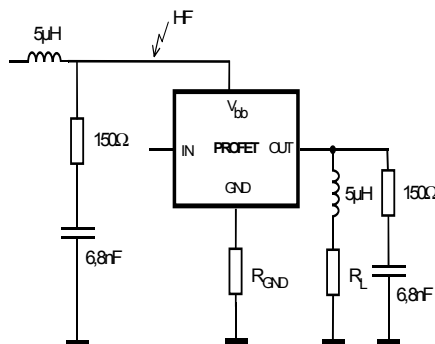
Typ. V_{bb} -Pin Susceptibility at DC-On/Off



Typ. V_{bb} -Pin Susceptibility at PWM-Mode

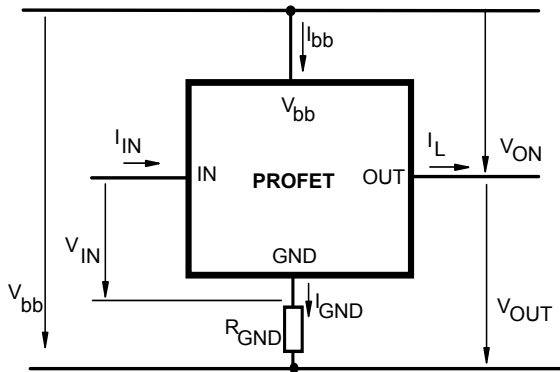


Test circuit:

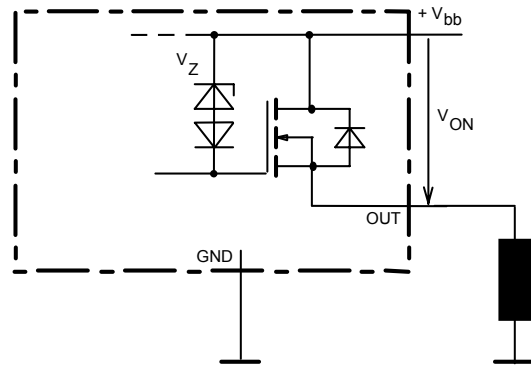


For defined decoupling and high reproducibility the same choke and the same 150Ω -matching network as for the emission measurement is used.

Terms

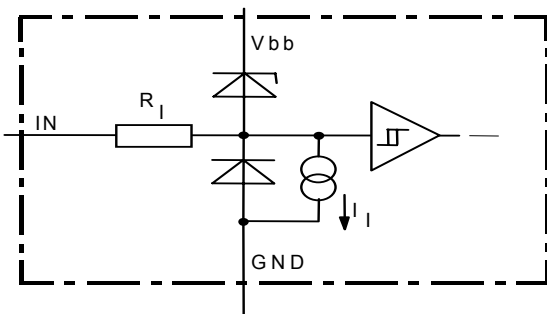


Inductive and overvoltage output clamp



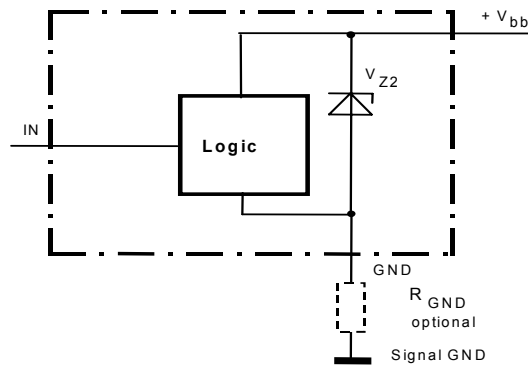
V_{ON} clamped to 63 V min.

Input circuit (ESD protection)



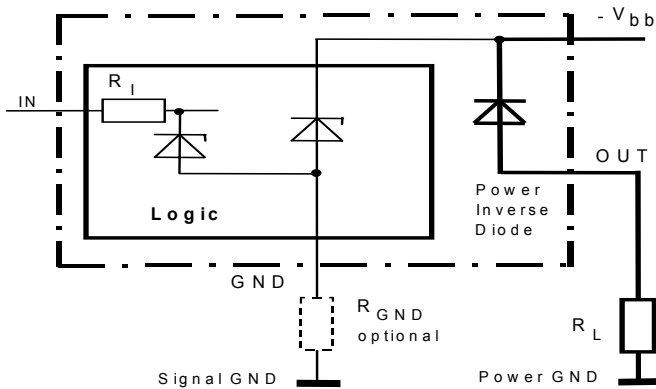
The use of ESD zener diodes as voltage clamp at DC conditions is not recommended

Overvoltage protection of logic part



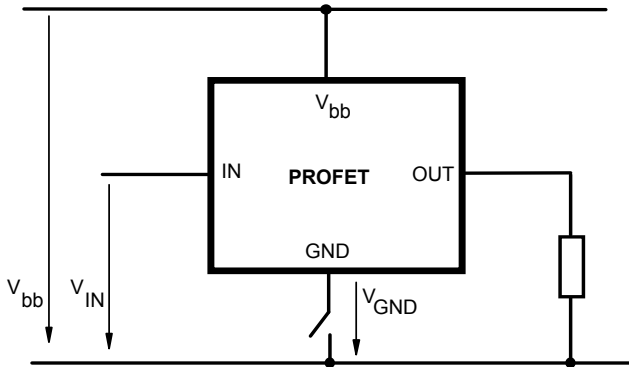
$V_{Z2}=V_{bb(AZ)}=47V$ min.,
 $R_I=3\text{ k}\Omega$ typ., $R_{GND}=150\Omega$

Reverse battery protection

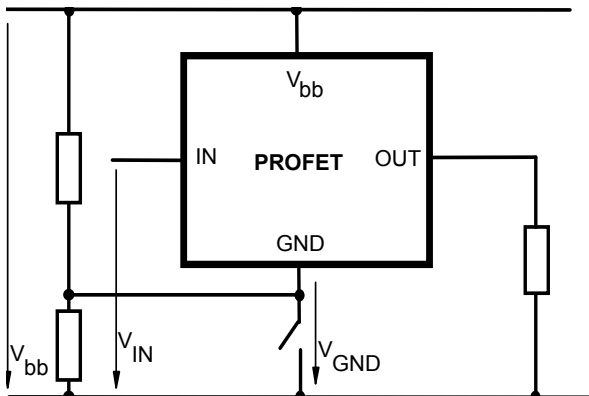


$R_{GND}=150\Omega$, $R_I=3\text{ k}\Omega$ typ.,
 Temperature protection is not active during inverse current

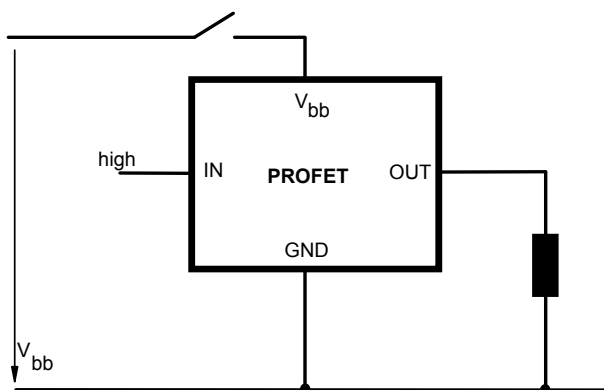
GND disconnect



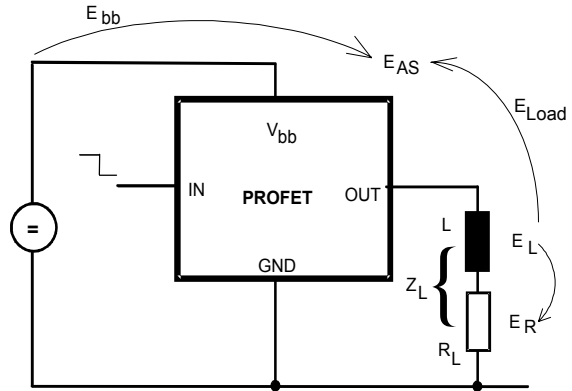
GND disconnect with GND pull up



V_{bb} disconnect with charged inductive load



Inductive Load switch-off energy dissipation



Energy stored in load inductance: $E_L = \frac{1}{2} * L * I_L^2$

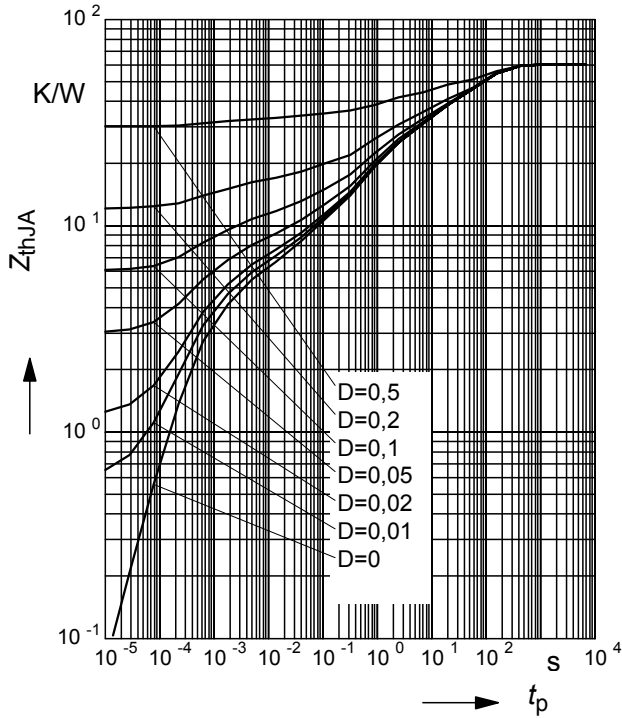
While demagnetizing load inductance, the energy dissipated in PROFET is $E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} * i_L(t) dt$, with an approximate solution for $R_L > 0\Omega$:

$$E_{AS} = \frac{I_L * L}{2 * R_L} * (V_{bb} + |V_{OUT(CL)}|) * \ln\left(1 + \frac{I_L * R_L}{|V_{OUT(CL)}|}\right)$$

Typ. transient thermal impedance

$Z_{thJA} = f(t_p)$ @ 6cm² heatsink area

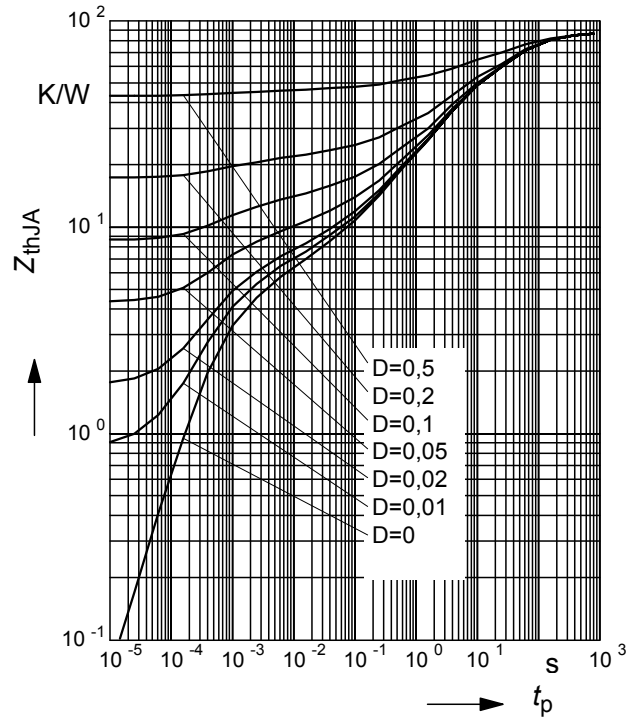
Parameter: $D = t_p / T$



Typ. transient thermal impedance

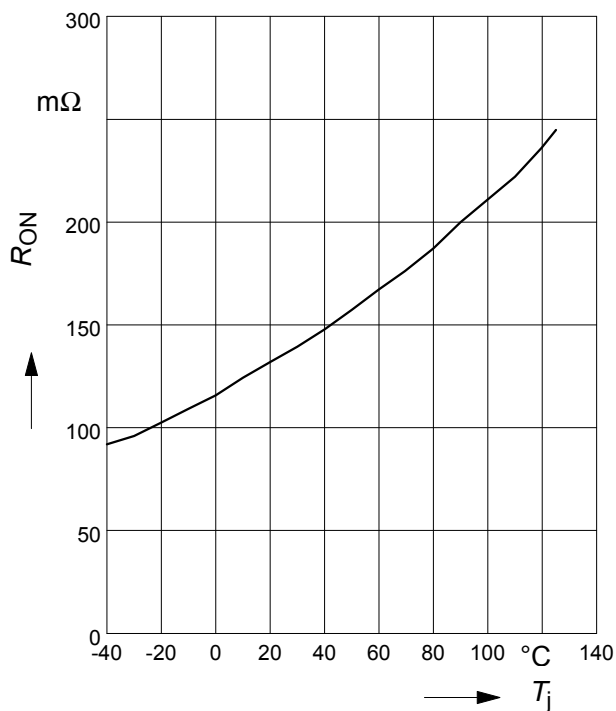
$Z_{thJA} = f(t_p)$ @ min. footprint

Parameter: $D = t_p / T$



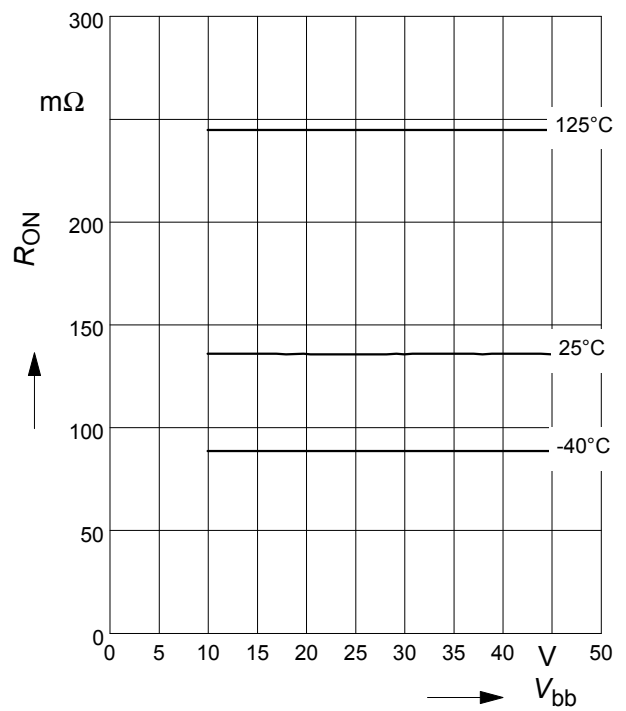
Typ. on-state resistance

$R_{ON} = f(T_j)$; $V_{bb} = 15\text{ V}$; $V_{in} = \text{high}$



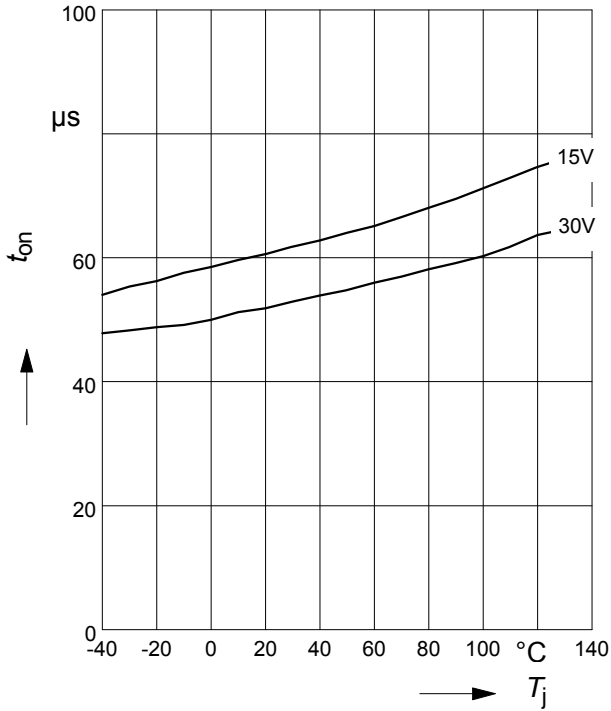
Typ. on-state resistance

$R_{ON} = f(V_{bb})$; $I_L = 0.5\text{ A}$; $V_{in} = \text{high}$



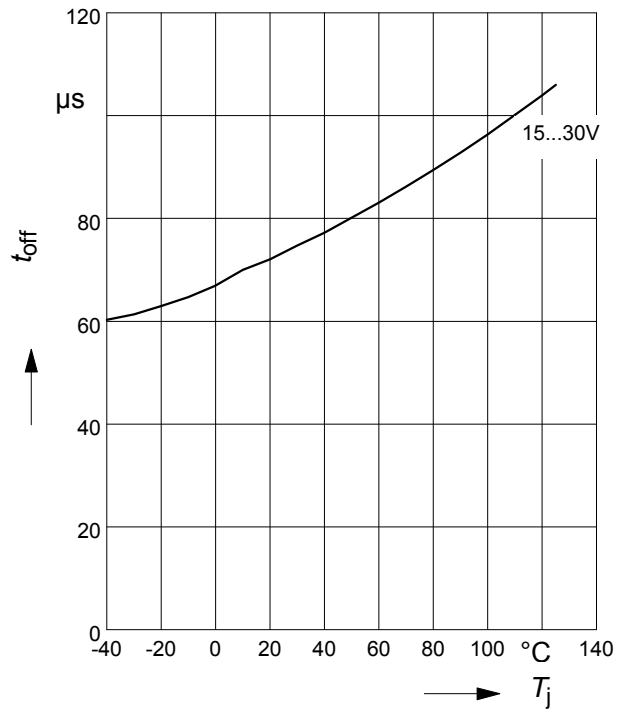
Typ. turn on time

$t_{on} = f(T_j); R_L = 47\Omega$



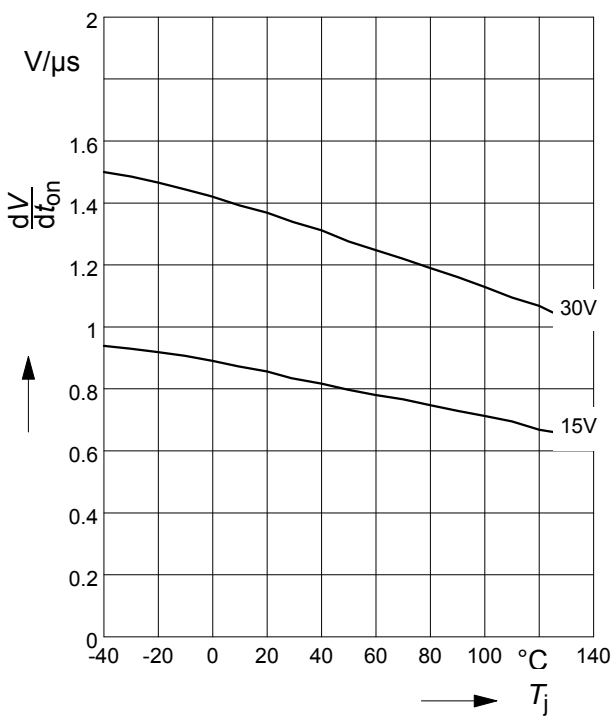
Typ. turn off time

$t_{off} = f(T_j); R_L = 47\Omega$



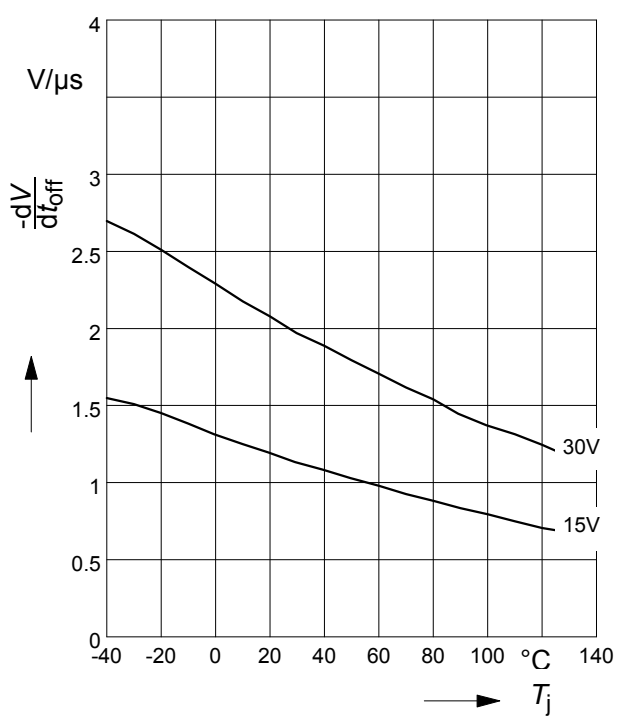
Typ. slew rate on

$dV/dt_{on} = f(T_j); R_L = 47\Omega$



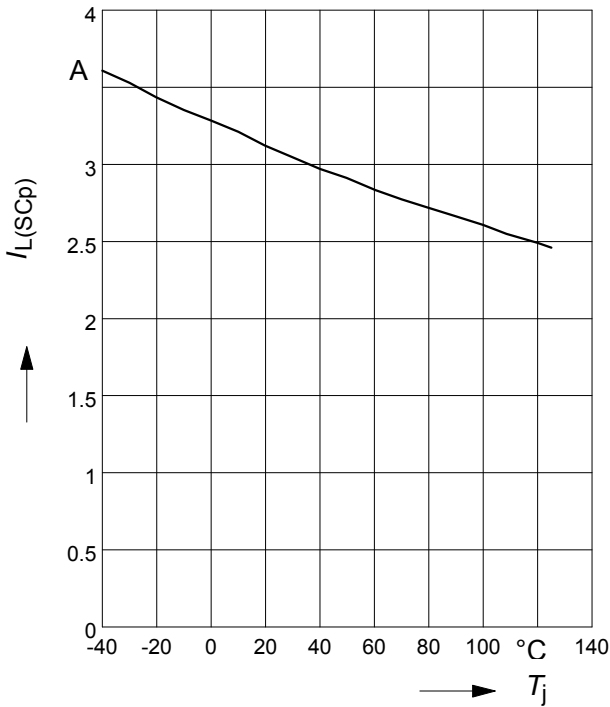
Typ. slew rate off

$-dV/dt_{off} = f(T_j); R_L = 47\Omega$



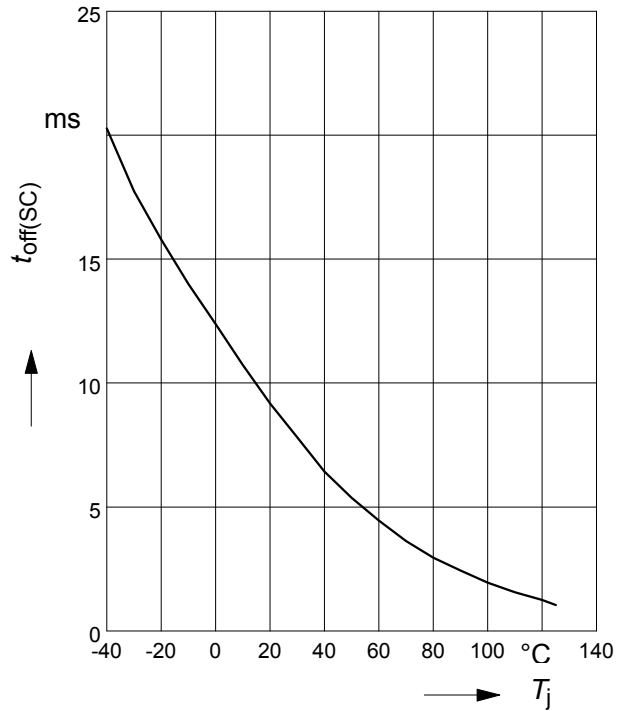
Typ. initial peak short circuit current limit

$I_{L(SCp)} = f(T_j)$; $V_{bb} = 20V$; $t_m = 150\mu s$



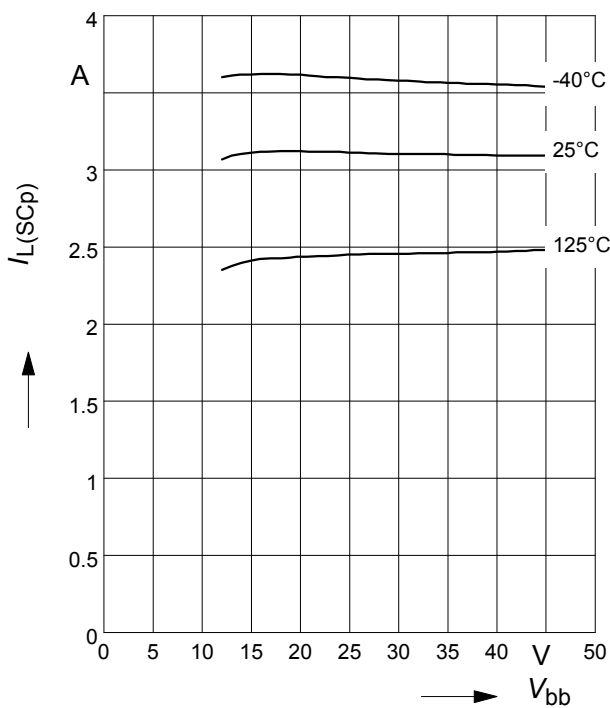
Typ. initial short circuit shutdown time

$t_{off(SC)} = f(T_{j,start})$; $V_{bb} = 20V$



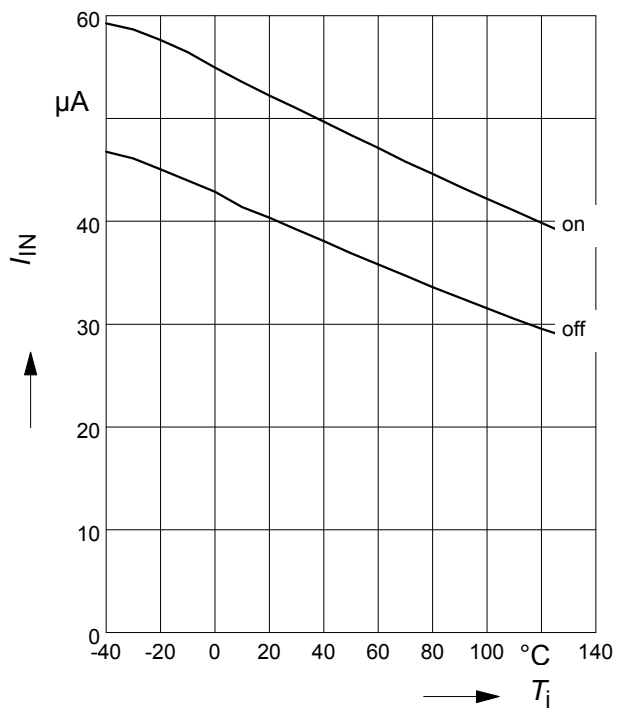
Typ. initial peak short circuit current limit

$I_{L(SCp)} = f(V_{bb})$; $t_m = 150\mu s$



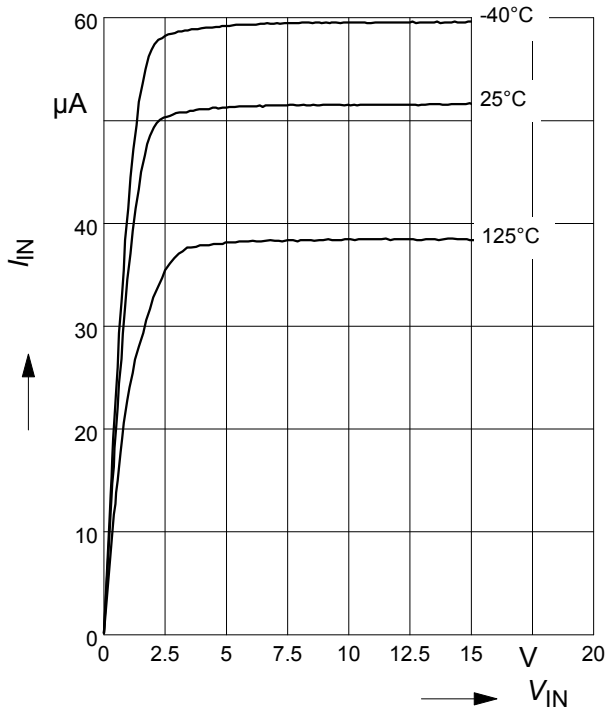
Typ. input current

$I_{IN(on/off)} = f(T_j)$; $V_{bb} = 15V$; $V_{IN} = \text{low/high}$
 $V_{INlow} \leq 1,8V$; $V_{INhigh} = 5V$



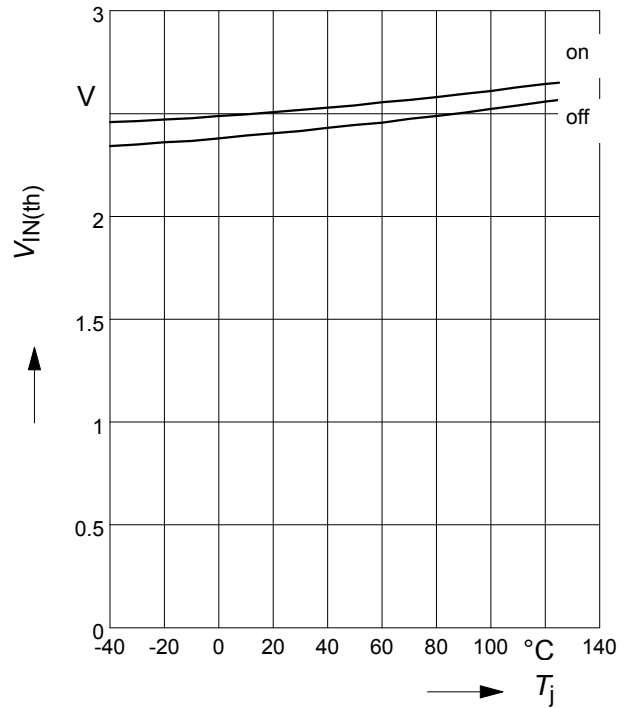
Typ. input current

$I_{IN} = f(V_{IN}); V_{bb} = 15\text{ V}$



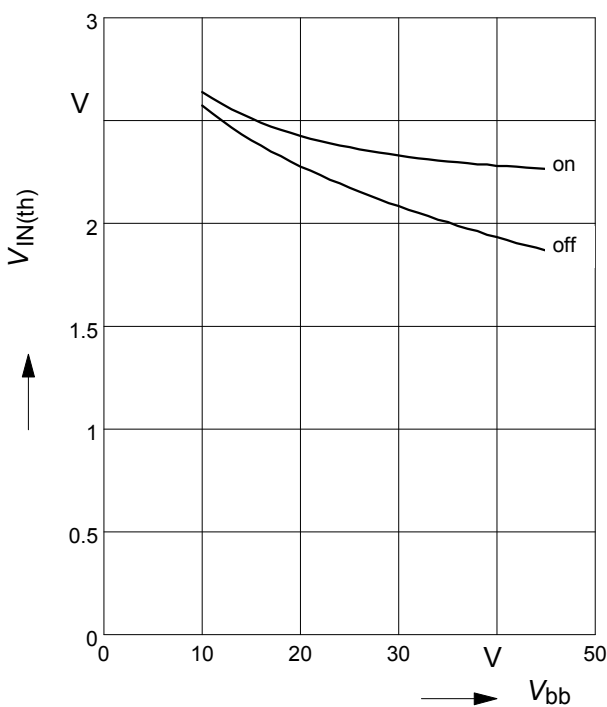
Typ. input threshold voltage

$V_{IN(th)} = f(T_j); V_{bb} = 15\text{ V}$



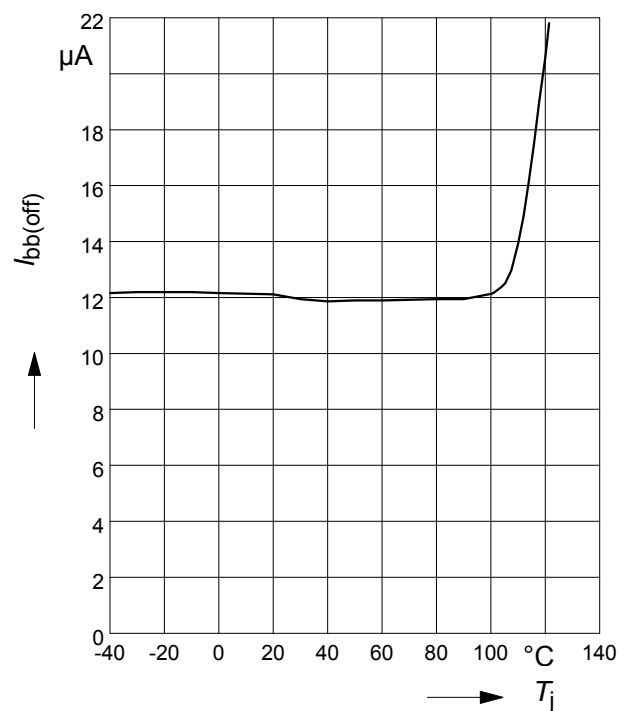
Typ. input threshold voltage

$V_{IN(th)} = f(V_{bb}); T_j = 25^\circ\text{C}$



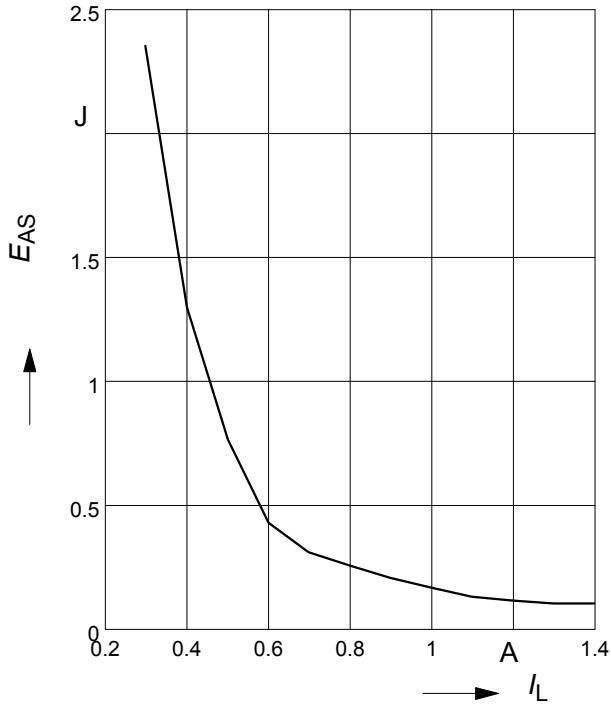
Typ. standby current

$I_{bb(off)} = f(T_j); V_{bb} = 32\text{ V}; V_{IN} \leq 1,2\text{ V}$



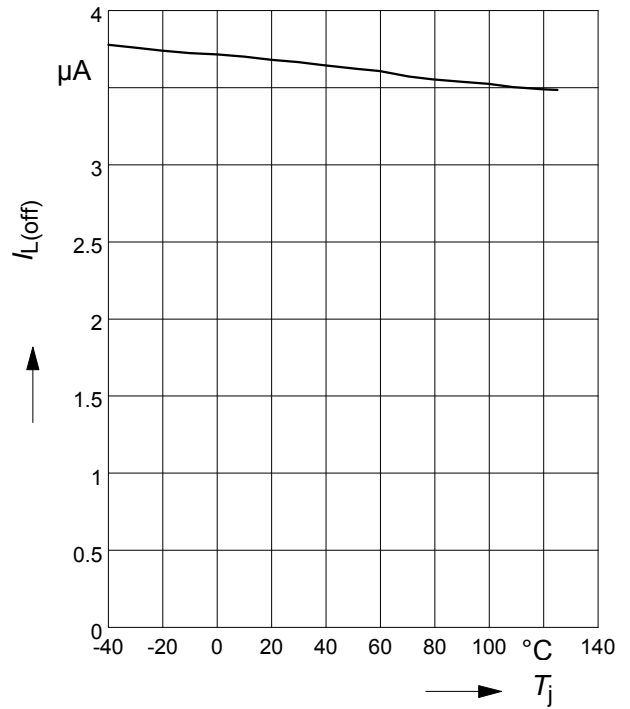
Maximum allowable inductive switch-off energy, single pulse

$E_{AS} = f(I_L); T_{jstart} = 125^{\circ}C$



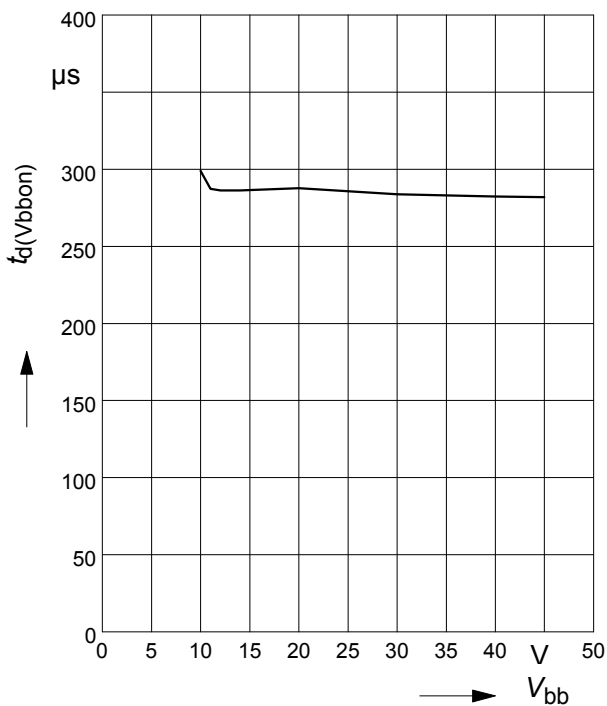
Typ. leakage current

$I_{L(off)} = f(T_j); V_{bb} = 32V; V_{IN} \leq 1,2 V$



Typ. input delay time at switch on V_{bb}

$t_d(V_{bbon}) = f(V_{bb})$



Timing diagrams

Figure 1a: Vbb turn on:

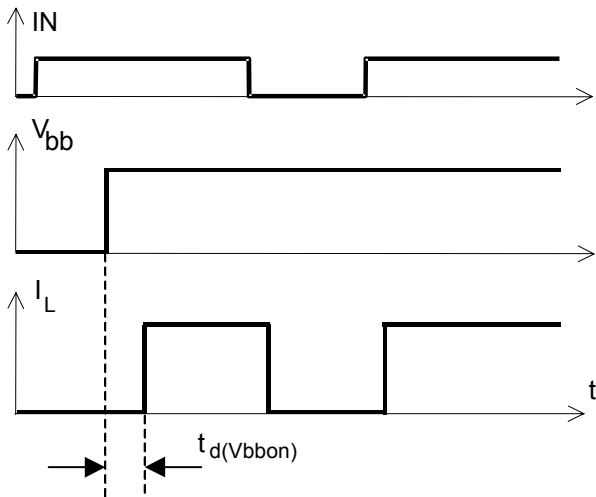


Figure 2b: Switching a lamp

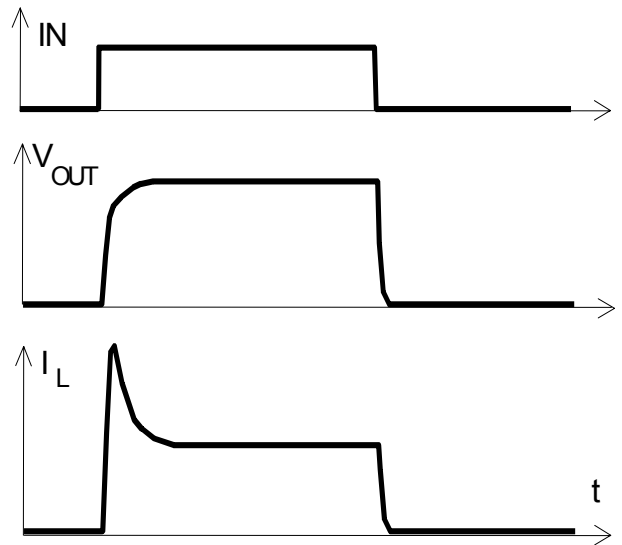


Figure 2a: Switching a resistive load, turn-on/off time and slew rate definition

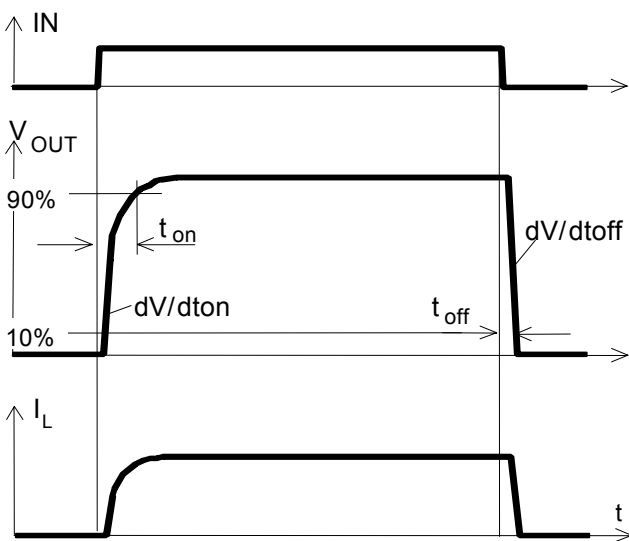


Figure 2c: Switching an inductive load

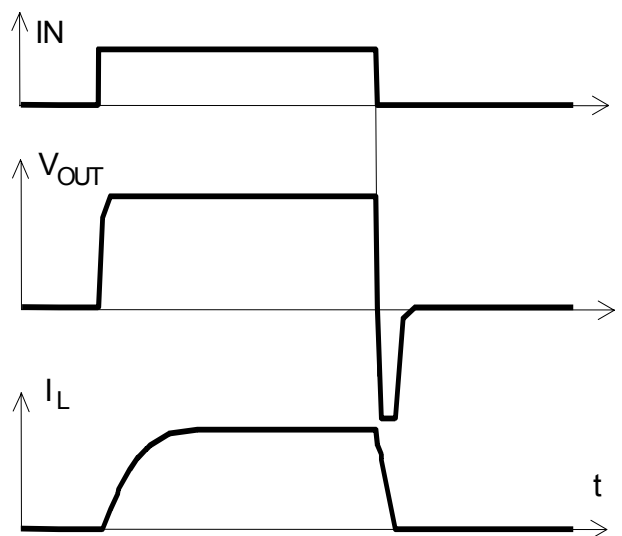
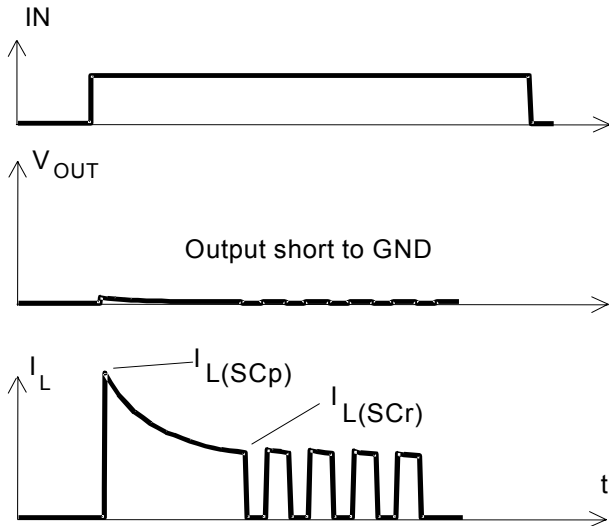


Figure 3a: Turn on into short circuit, shut down by overtemperature, restart by cooling



Heating up of the chip may require several milliseconds, depending on external conditions.

Figure 3b: Short circuit in on-state shut down by overtemperature, restart by cooling

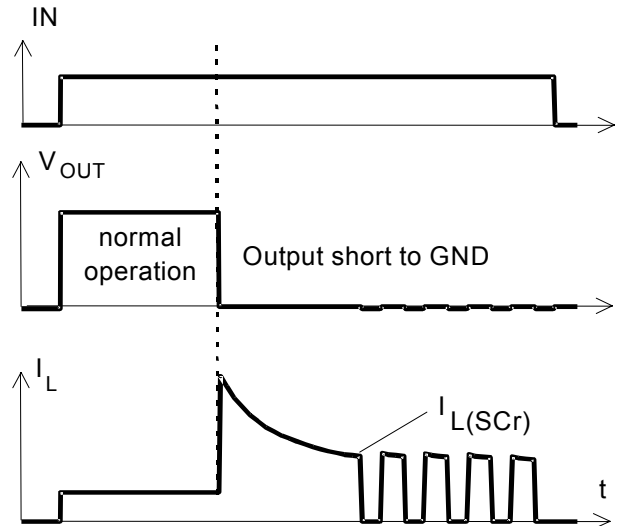


Figure 4: Overtemperature: Reset if $T_j < T_{jt}$

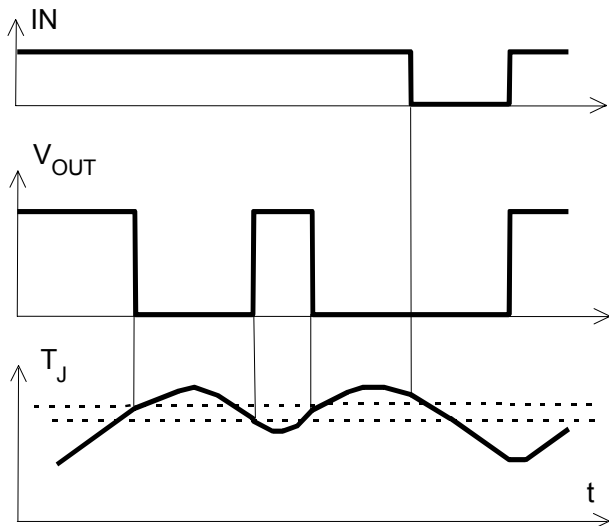
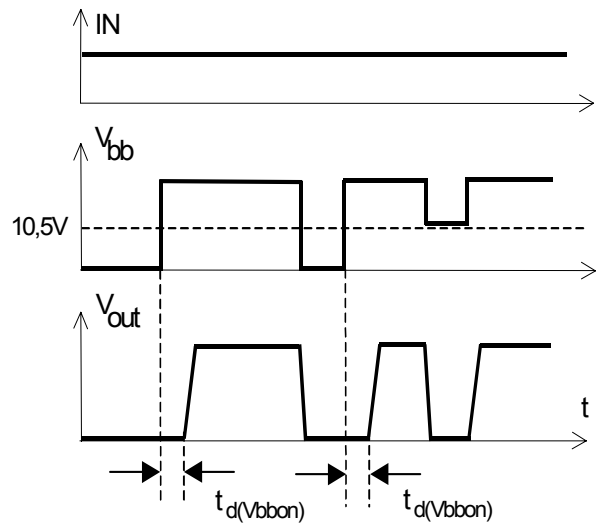


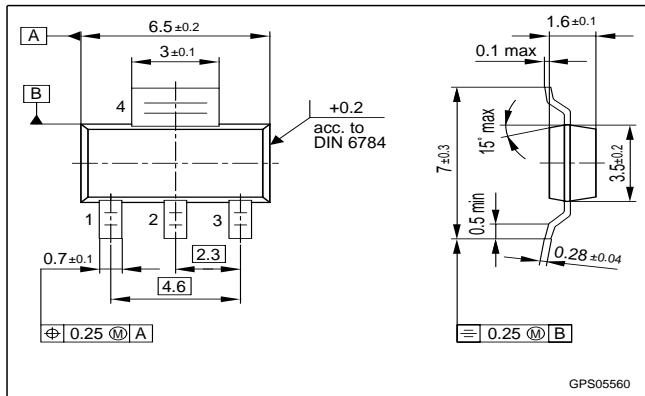
Figure 5: Undervoltage shutdown and restart



Package and ordering code

all dimensions in mm

| | |
|-------------------------------------|-------------|
| Sales code | ITS 4142N |
| Ordering code, standard (1000 pcs.) | SP000221218 |



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